

HB 砷化鎵單晶錠及單晶片 (直徑有: 2", 2.5", 3")

Parameters of **HB-GaAs Ingot & Wafer**

Conduct Type	Semi-conducting					
Dopant	Si					
Diameter	50.8±0.4mm; 63.5±0.4mm; 76.2±0.4mm					
Wafer Orientation	(100) 15°±0.5° off toward (111)A					
Carrier Concentration	(0.4-4)×10 ¹⁸ cm ⁻³					
Resistivity (at RT)	(0.8-9)×10 ⁻³ Ωcm					
Mobility	> 1200cm ² /Vs					
Etch Pit Density (EPD)	≤5000cm ⁻²					
OF / IF	EJ / US					
Surface Finish	Side1	Polished	Side2	L/E	Epi-Ready	Yes
Packing	Single or Cassette					

- Other orientation, thickness, or other parameters available upon request.

VGF 砷化鎵單晶錠及單晶片 (直徑有: 2", 3", 4")

Parameters of **VGF-GaAs Ingot & Wafer**

Conduct Type	Semi-conducting					
Dopant	Si					
Diameter	50.8±0.4mm; 76.2±0.4mm; 100±0.4mm					
Wafer Orientation	(100)					
Carrier Concentration	(0.4-4)×10 ¹⁸ cm ⁻³					
Resistivity (at RT)	(0.8-9)×10 ⁻³ Ωcm					
Mobility	> 1200cm ² /Vs					
Etch Pit Density (EPD)	≤5000cm ⁻²					
OF / IF	EJ / US					
Surface Finish	Side1	Polished	Side2	L/E	Epi-Ready	Yes
Packing	Single or Cassette					

Conduct Type	Semi-insulating					
Dopant	Undoped					
Diameter	50.8±0.4mm; 76.2±0.4mm; 100±0.4mm					
Wafer Orientation	(100)					
Resistivity (at RT)	> 10 ⁷ Ωcm					
Mobility	> 5000cm ² /Vs					
Etch Pit Density (EPD)	≤10000cm ⁻²					
OF / IF	EJ / US					
Surface Finish	Side1	Polished	Side2	L/E	Epi-Ready	Yes
Packing	Single or Cassette					

- Other orientation, thickness, or other parameters available upon request.

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